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IN THE DRAWINGS:

The attached seven (7) sheets of Drawings include changes to Figs. 5-11. These seven (7) sheets, which includes Figs. 5-11, replace the original sheets including Figs. 5-11.

Attachment: seven (7) Replacement Sheets.

REMARKS


Claims 12-28 are pending in this application. By this Preliminary Amendment, Applicants AMEND the specification and the abstract of the disclosure, CANCEL claims 1-11 and ADD new claims 12-28.

Applicants have attached hereto a Substitute Specification in order to make corrections of minor informalities contained in the originally filed specification. Applicants' undersigned representative hereby declares and states that the Substitute Specification filed concurrently herewith does not add any new matter whatsoever to the above-identified patent application. Accordingly, entry and consideration of the Substitute Specification are respectfully requested.

The changes to the specification have been made to correct minor informalities to facilitate examination of the present application.

Applicants respectfully submit that this application is in condition for allowance. Favorable consideration and prompt allowance are respectfully solicited.

Respectfully submitted,



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DESCRIPTION

SURFACE ACOUSTIC WAVE DEVICE

BACKGROUND OF THE INVENTION1. Technical Field of the Invention

[0001] —The present invention relates to a surface acoustic wave device, and more particularly, to a surface acoustic wave device including~~containing~~ a surface acoustic wave element.

2. Description of the Related ArtIn Background Art

[0002] —~~Up to now, in a~~ conventional balanced-type SAW (surface acoustic wave) filter having an unbalanced-to-balanced-type filter of a first stage and a balanced-to-balanced-type filter of a second stage that are cascade-connected, ~~a structure in which~~ signal wirings for connecting the balanced terminals of the filters are disposed between the stages and a ground pad connected to the other terminal of an unbalanced terminal IDT (interdigital transducer, comb-shaped electrode) of the first stage is disposed between the signal wirings ~~has been proposed.~~

[0003] —Fig. 5 is a top view of a substrate of ~~contained in a~~ surface acoustic wave device of a related example. The substrate 1210 is a LiTaO₃ single crystal substrate and, ~~on its main surface 1212, as shown in Fig. 5,~~ a metal film having ~~of~~ a fixed pattern is provided on the main surface 1212, as shown in Fig. 5. ~~formed.~~ That is, a balanced-type SAW filter is provided, in which a longitudinally coupled ~~, in which a longitudinal coupling resonator-type surface~~ acoustic wave filter 1220 of the first stage and a longitudinally coupled ~~longitudinal coupling resonator-type surface~~ acoustic wave

filter 1230 of the second stage are cascade-connected, a pad 1251 ~~defines is used as~~ an unbalanced terminal, and pads 1252 and 1253 ~~define are used as~~ balanced terminals, ~~is constituted~~. In an area enclosed by the filters 1220 and 1230 and wirings 1241 and 1242 for cascade-connecting the filters 1220 and 1230, a ground pad 1256 connected to an IDT 1223 including the unbalanced terminal 1251 is disposed (see, for example, Japanese Unexaminedsee Patent Application Publication No. 2002-300004Document-1).

[0004] ~~_____~~—Furthermore, in recent years, there has been a the requirement for having a balanced-to-unbalanced conversion function or a so-called balun function includedecontained in a surface acoustic wave filter used in the RF stage of a portable telephone ~~has become strong~~. Lately, in particular, a longitudinally coupledlongitudinal coupling resonator-type surface acoustic wave filter which provides a ~~can cope with a~~ high-frequency wave and also which provides ~~can easily cope with a~~ balanced-to-unbalanced conversion function has become more commonmain-stream as a bandpass filter of the RF stage of a portable telephone.

[0005] ~~_____~~—The surface acoustic wave filter having a balanced-to-unbalanced conversion function is connected to a mixer IC (hereinafter, referred to as a balanced-type mixer IC) having a balanced or differential input and output. When this balanced-type mixer IC is used, the effect of noise is reduced and the output is ~~can be~~ stabilized. Thus, this ~~, and thus the~~ surface acoustic wave filter is ~~has been often used to improve the for improvement of~~ characteristics of portable telephones ~~in recent years~~.

[0006] ~~A~~—~~Regarding such a~~ surface acoustic wave filter having a balanced-to-unbalanced conversion function may includeecontained, various structures. Each of the various structures has benefits and detriments ~~can be considered and may be many of them have been~~ proposed. ~~These have merits and demerits according to each structure~~

~~and are properly used in accordance with the intended uses and user's~~
requirements. ~~One known~~~~As one of them, there is one~~ structure
includes in which balanced terminals that are connected to both
terminals of one IDT.

[0007] ——— For example, in Fig. 6, an element chip 30 of such a
surface acoustic wave filter is schematically shown. The surface
acoustic wave filter is configured ~~made~~ to have a balanced-to-
unbalanced conversion function ~~in such a way that~~ both ends of the
middle IDT 1 of a longitudinally coupled~~longitudinal coupling~~
resonator-type surface acoustic wave filter element 6
including~~containing~~ three IDTs 1, 2, and 3 and two reflectors 4 and 5
are connected to balanced signal terminals 11 and 12, respectively,
and such that one end of each of the left and right IDTs 2 and 3 is
connected to an unbalanced signal terminal 13 through an IDT 7 of a
surface acoustic wave resonator 10 in which reflectors 8 and 9 are
disposed on either side of the IDT 7. In the surface acoustic wave
filter, the other ends of the IDTs 2 and 3 are connected to a ground
terminal.

[0008] ——— The element chip 30 is housed in a package which can be
divided into an upper portion and a lower portion in the bottom-side
portion. Fig. 7 shows the upper surface of the upper portion 33 of
the package bottom portion 31 in which the element chip 30 is mounted,
Fig. 8 shows the upper surface of the lower portion 36 of the package
bottom portion 31, and Fig. 9 shows the lower surface (bottom surface
of the package) of the lower portion 36 of the package bottom portion
31.

[0009] ——— As shown in Fig. 7, wiring patterns (lands) 42 to 45 are
exposed in the die attachment portion 41 of the upper portion 33 of
the package bottom portion 31 and bump-connected to the terminals
(pads) of the element chip 30 by a bump 39, shown by a white circle in
Figs. 6 and 7. In Fig. 7, via holes 46 and 47, shown by black circles,

pass through the upper portion 33 of the package bottom portion 31 and the wiring patterns 45 and 44 and wiring patterns 61 and 63 of the lower portion 36 shown in Fig. 8 are connected. Among external terminals shown in Fig. 9, the right middle external terminal 56 is an unbalanced signal terminal, the left upper and lower external terminals 52 and 53 are balanced signal terminals, and the other external terminals 54 and 55 are ground terminals. The external terminal 56 defining as an unbalanced signal terminal is connected to the unbalanced signal wiring pattern 42 through a castellation 48. The external terminals 52 and 53 defining as balanced signal terminals are connected to the balanced signal wiring patterns 43 and 44 through castellations 49 and 50.

[0010] Finally, corresponding to the locations~~disposition~~ of the first and second balanced signal terminals (pads) 11 and 12 on the element chip 30 shown in Fig. 6, as shown in Fig. 7, in the flip-chip mounting package of the element chip 30, the first balanced signal terminal wiring pattern (pad) 43 is disposed~~formed~~ in the middle of one side of the package, and the second balanced signal terminal wiring pattern (land) 44 is disposed~~formed~~ in the corner portion close to the first balanced signal terminal wiring pattern (land) 43. In the element chip 30, a signal line 1a ~~for~~ connecting one end of the IDT 1 and a first balanced signal terminal 11 and a signal line 1b ~~for~~ connecting the other end of the balanced ITD 1 and a second balanced signal terminal 12 are asymmetrically disposed, and thus become ~~unsymmetrical and, when they are unaltered as they are, the balancing is deteriorated. deteriorates.~~ Then, as shown in Fig. 9, the external terminals 52 and 53 as the first and second balanced signal terminals are disposed so as to be symmetrical around the central axis of the package, and the balancing is adjusted by altering the path difference in the package between a signal line connected to the external terminal 52 defining as the first balanced signal terminal and a

signal line connected to the external terminal 53 defining as the
second balanced signal terminal (see, for example, Japanese Unexamined
Patent Application Publication No. 2002-271168~~Document-2~~).

[0011] —The surface acoustic wave filter package shown in Figs.
6 to 9 can be also used for mounting an element chip 60 including
~~having a structure in which two longitudinally coupled longitudinal~~
~~coupling~~ resonator-type surface acoustic wave filter elements 66 and
68 having three IDTs 66a, 66b, and 66c, and 68a, 68b, and 68c and two
reflectors 66s and 66t, and 68s and 68t, respectively, as shown in Fig.
22. That is, the element chip 30 shown in Fig. 1 and the element chip
60 shown in Fig. 22 have the same external dimensions and the same
terminal (pad) configuration.

[0012] —In Japanese Unexamined Patent Application Publication
No.2002-204243~~Document-3~~, a float balanced-type surface acoustic wave
filter in which the balancing is improved ~~in such a way that~~ two
terminals extending on either side in the direction perpendicular to
the surface acoustic wave propagation direction of the middle ITD of a
longitudinally coupled longitudinal coupling resonator-type surface
acoustic wave filter element are connected to balanced signal
terminals, ~~that~~ IDTs on both sides are connected to unbalanced signal
terminals by using two unbalanced signal lines, and ~~that~~ one balanced
signal line and one unbalanced signal line intersect in three
dimensions through an insulating film is disclosed.

~~Patent Document 1: Japanese Unexamined Patent Application Publication~~
~~No. 2002-300004~~

~~Patent Document 2: Japanese Unexamined Patent Application Publication~~
~~No. 2002-271168~~

~~Patent Document 3: Japanese Unexamined Patent Application Publication~~
~~No. 2002-204243~~

[0013] —As in the related example shown in Fig. 5, when two
elements are cascade-connected and a ground pad is disposed between

stages, since stray capacitance between the wiring for the cascade connection and the ground pad is large, there is a problem in that the insertion loss in the passband is large.

~~—In consideration of such factors, it is a first object of the present invention to provide a surface acoustic wave device having two elements cascade-connected in which insertion loss in the passband can be reduced.~~

[0014] —Furthermore, in a surface acoustic wave filter of a ~~structure~~ having a balanced-to-unbalanced conversion function which includes contained by connecting balanced signal terminals that are connected to the terminals on both sides of one IDT as by a method disclosed in Japanese Unexamined Patent Application Publication No. 2002-271168) ~~Document 2~~, since the structure of the package is complicated and specific, the configuration of the package ~~is becomes~~ limited to the element structure.

[0015] Accordingly, for example, a surface acoustic wave filter 70 ~~having the structure shown in Fig. 10~~ includes two longitudinally coupled ~~in which two longitudinal coupling~~ resonator-type filter elements 71 and 72 having three IDTs 71a, 71b, and 71c, and 72a, 72b, and 72c and two reflectors 71s and 71t, and 72s and 72t that are cascade-connected, + one end of the middle IDT 71a of one longitudinally coupled ~~longitudinal coupling~~ resonator-type filter element 71 is connected to an unbalanced terminal 73, + and one end (one bus bar) of the middle IDT 72a of the other longitudinally coupled ~~longitudinal coupling~~ resonator-type filter element 72 is divided into two bus bars and the two bus bars are connected to balanced signal terminals 74 and 75.

[0016] Another, a surface acoustic wave filter 80 ~~having the structure shown in Fig. 11~~ includes in which, regarding two sets of surface acoustic wave filter elements 81, 82, 83, and 84 having three IDTs 81a, 81b, and 81c; 82a, 82b, and 82c; 83a, 83b, and 83c; and 84a,

84b, and 84c and two reflectors 81s and 81t; 82s and 82t; 83s and 83t; and 84s and 94t that are cascade-connected, one end of each of the middle IDTs 81a and 83a of the one-surface acoustic wave filter elements 81 and 83 is connected to balanced terminals 85 and 86, and one end of each of the other surface acoustic wave filter elements 82 and 84 of the sets is connected to an unbalanced terminal 87. However, with this configuration, ~~and other~~ surface acoustic wave filters cannot share the package with a surface acoustic wave filter having a balanced-to-unbalanced conversion function of another structure different in terms of the way surface acoustic wave elements are coupled.

[0017] —Moreover, since the signal lines inside the package are asymmetrical~~become unsymmetrical~~, the affect of parasitic capacitance, isete.~~becomes~~ different between balanced signal terminals, and, as a result, there is a problem in that the balancing between balanced signal terminals is deteriorated~~worsened~~.

[0018] —In a surface acoustic wave filter in Japanese Unexamined Patent Application Publication No.2002-20424~~Document~~-3, an intersection is performed by providing~~forming~~ a balanced signal line on a piezoelectric substrate and providing~~forming~~ an unbalanced signal line on an insulating film disposed~~formed~~ on the balanced signal line. Accordingly, the difference between the parasitic capacitance and bridge capacitance entering the two balanced signal terminals increases and the balancing cannot be sufficiently~~fully~~ improved.

SUMMARY OF THE INVENTION

[0019] —To overcome the problems described above, preferred embodiments ~~In consideration of such factors, it is a second object~~ of the present invention ~~to provide~~ a surface acoustic wave device including two cascade-connected elements in which insertion loss in

the passband is greatly reduced, and a surface acoustic wave filter
which can be housed in~~is easy to share~~ a common package with a surface
acoustic wave filter having~~of~~ another configuration, structure and in
which has greatly improved ~~the~~ balancing between balanced signal
terminals. ~~is improved.~~ That is, preferred embodiments of the
present invention ~~is to~~ provide a surface acoustic wave device in
which the characteristics are greatly ~~can be~~ improved.

[0020] A surface acoustic wave device according to a preferred
embodiment of the present invention includes~~Disclosure of Invention~~

~~The present invention provides a surface acoustic wave device~~
~~having the following structure. acoustic wave device comprises a~~
substrate, ~~+~~ a plurality of terminals disposed on the substrate and
including~~containing~~ at least an unbalanced terminal and two balanced
terminals, ~~+~~ and at least one surface acoustic wave element disposed
between the unbalanced terminal and the balanced terminals on the
substrate. In this ~~the~~ surface acoustic wave device, different signal
lines connected to the same surface acoustic wave element intersect
through an insulating film.

[0021] The ~~In the above structure,~~ the substrate may be a
piezoelectric substrate in which the entire~~whole~~ substrate is made of
a piezoelectric material or a piezoelectric substrate in which a thin
film of piezoelectric material (piezoelectric thin film) is
disposed~~formed~~ on the main body of a substrate made of non-
piezoelectric material. In the latter case, ~~at least a~~ piezoelectric
thin film is provided~~formed~~ in at least the portion of a surface
acoustic wave element. A balanced signal is input to or output from a
balanced terminal and an unbalanced signal is input to or output from
an unbalanced terminal.

[0022] When ~~As in the above structure,~~ when different signal
lines connected to the surface acoustic wave elements intersect

through an insulating film, the length of the signal lines is reduced as compared to ~~when can be more shortened than in the case where the~~ signal lines are disposed so as set not to intersect, and the restrictions on the locations of setting the signal lines are greatly reduced~~can be eased.~~

[0023] ~~_____~~—In this mannerway, for example, when a balanced type surface acoustic wave filter is constructed by connecting two surface acoustic wave elements using signal lines, the insertion loss is~~can be~~ reduced ~~in such a way that~~ the lengths of the signal lines ~~extending~~~~connecting~~ between the surface acoustic wave elements are shortened by reducing~~narrowing~~ the space between the two surface acoustic wave elements, and by not providing~~without containing~~ pads between the surface acoustic wave elements.

[0024] ~~_____~~—Furthermore, with~~regarding~~ the signal lines ~~extending~~~~connecting~~ between the surface acoustic wave elements and the signal lines ~~extending~~~~connecting~~ between the surface acoustic wave elements and the terminals, since the restrictions on the locations of setting the lines are reduced, it is easier to provide a ~~eased, it becomes easy to have the package for common use.~~

~~_____~~—Preferably, the insulating film is polyimide.

[0025] ~~_____~~—Since the relative dielectric constant of the polyimide is sufficiently small as compared to ~~in comparison with~~ the relative dielectric constant of the piezoelectric substrate, stray capacitance is~~can be~~ reduced.

[0026] According to a first preferred embodiment~~As a preferable first mode~~, at least two of the surface acoustic wave elements are provided~~contained~~. One of the two surface acoustic wave elements defines~~(hereinafter, referred to as a first element which)~~ is connected to the unbalanced terminal and a ground terminal so as to be grounded with ~~(hereinafter, referred to as a ground pad) for grounding with the different signal lines.~~ The other of the two surface

acoustic wave elements defines a second element. At least two of the signal lines define line ~~(hereinafter, referred to as a signal wirings~~ for connecting the ~~other of the two surface acoustic wave elements~~ ~~(hereinafter, referred to as a second element)~~ and the first element are ~~formed~~. At least one of the signal wirings wiring and the signal line defining ~~(hereinafter, referred to as a ground wiring arranged to connect)~~ for connecting the ground terminalpad and the first element intersect through the insulating film. The ground terminalpad is disposed outside an area enclosed by the first element, the second element, and the signal wirings.

[0027] ——— In the related device, the ground terminal is disposedpad is formed inside an area enclosed by the first element, the second element, and the signal wirings and the insertion loss in the passband is thereby increases. ~~However~~But, according to the above-described configuration construction, the stray capacitance between the ground terminalpad and the signal lines is minimized ~~reduced~~ and, as a result, the insertion loss in the passband ~~can be reduced in such a way that the ground pad is greatly reduced due to~~ the ground terminal being disposedformed outside an area enclosed by the first element, the second element, and the signal wirings.

[0028] ——— Preferably, the first element includescontains three IDTs disposed in aso as to have the same propagation direction of a surface acoustic wave, and the unbalanced terminal and the ground terminalpad are connected to the middle IDT of the three IDTs. The second element includescontains three IDTs disposed inso as to have the ~~same~~ propagation direction of a surface acoustic wave, and two balanced terminals are connected to the middle IDT of the three IDTs. The IDTs on either side of the middle IDT of the first element and the IDTs on either side of the middle IDT of the second element are connected by the signal wirings.

[0029] ——— According to the above configurationstructure, the

insertion loss in the passband of a balanced type SAW filter in which the longitudinally coupled~~longitudinal coupling~~ resonator-type SAW filter elements (first element and second element) are cascade connected is greatly~~can be~~ reduced.

[0030] ———— Preferably, two sets of the first element, the signal wirings, and the second element are provided~~formed~~ on the substrate. The first element of each set includes~~contains~~ three IDTs disposed in~~so as to have~~ the same propagation direction of a surface acoustic wave, and the unbalanced terminal and the ground terminal~~pad~~ are connected to the middle IDT of the three IDTs. The second element of each set includes~~contains~~ one IDT connected to one of the balanced terminals different from that in the other sets. In each set, the two signal wirings connect the IDTs on either side of the first element and the IDT of the second element. The first elements of the two sets are in opposite phase to each other.

[0031] ———— According to the above configuration~~structure~~, the longitudinally coupled~~longitudinal coupling~~ resonator-type SAW filter (first element) connected to a balanced pad and the one-port SAW resonator (second element) are connected in series, two sets of these are connected in parallel, the longitudinally coupled~~longitudinal coupling~~ resonator-type SAW filter (first element) is arranged~~made~~ to be in opposite phase, and the one-port SAW resonator (second element) is used as a trap. Thus, in a balanced type SAW filter having filter characteristics improved, the insertion loss in the passband is greatly~~can be~~ reduced.

[0032] ———— Preferably, the ground wiring includes~~contains~~ a first layer that is not disposed in the vicinity of the ~~formed excluding the~~ insulating film and ~~its vicinity and~~ a second layer that is disposed on the vicinity of the ~~formed including the~~ insulating film ~~and its vicinity~~.

[0033] ———— According to the above-described structure, regarding

the ground wiring, since two layers are disposed~~put~~ one on top of another around the insulating film, the ground residual impedance is decreased and the attenuation outside the band is improved.

Furthermore, the signal wiring may include~~can be formed using~~ only one layer, because~~since~~ two layers are not required to be disposed~~put~~ one on another around the insulating film, the signal wiring is~~can be~~ shortened, + and the size is~~can be~~ reduced by shortening the distance between the first element and the second element.

[0034] According to a ~~As a preferable~~ second preferred embodiment~~mode~~, at least two surface acoustic wave elements are connected to each other~~are contained~~. One of the two surface acoustic wave elements (hereinafter, referred to as a first surface acoustic wave element) is a longitudinally coupled~~longitudinal coupling~~ resonator-type surface acoustic wave element having three IDTs disposed along the propagation direction of a surface acoustic wave, and the middle IDT ~~out~~ of the three IDTs is connected to the two balanced signal terminals through the two signal lines (hereinafter, referred to as first and second signal lines). The two balanced signal terminals are disposed on either side of the central axis of the substrate substantially in parallel to the direction in which the two surface acoustic wave elements are arranged. At least one of the first and second signal lines is disposed on the insulating film formed on the substrate.

[0035] —In the above-described structure, when at least one of the first and second signal lines and the signal line connecting between the surface acoustic wave elements intersect, in this intersecting portion, a three-dimensional intersection is provided~~performed~~ through an insulating film.

[0036] —According to the above-described structure, the package can be commonly used by arranging the balanced signal terminals at the same locations as in a surface acoustic wave filter having ~~of~~ another

~~structure-different configuration in the condition~~ for coupling the surface acoustic wave element. Furthermore, regarding the parasitic capacitance and bridge capacitance entering each of the two balanced signal terminals, the difference between them is reduced by disposing the signal lines connected to the balanced signal terminals on an insulating film and thus, the balancing can be improved.

[0037] — Preferably, the two balanced signal terminals are disposed so as to be substantially symmetrical around the central axis of the substrate.

[0038] — According to the above-described structure, since the balanced signal terminals are disposed substantially in the same location as in a surface acoustic wave filter having ~~of another configuration structure~~ in which the balanced signal terminals are symmetrically disposed, ~~it is excellent in common use of the package~~ can be used.

[0039] — Preferably, the second surface acoustic wave element is disposed in the propagation direction of a surface acoustic wave and is a longitudinally coupled ~~longitudinal coupling~~ resonator-type surface acoustic wave filter element having three IDTs cascade-connected to the first surface acoustic wave element.

[0040] — According to the above-described structure, the attenuation outside the passband can be increased.

[0041] — Preferably, the second surface acoustic wave element is one or a plurality of surface acoustic wave resonator elements connected together.

[0042] — According to the above-described structure, the attenuation outside the passband is further ~~can be~~ increased.

[0043] According to a — ~~As a preferable third preferred embodiment~~, the surface acoustic wave element is a longitudinally coupled ~~longitudinal coupling~~ resonator-type surface acoustic wave filter element including ~~containing~~ three IDTs disposed along the

propagation direction of a surface acoustic wave, and the middle IDT ~~out~~ of the three IDTs is connected to the two balanced terminals through the signal lines (hereinafter, referred to as first and second signal lines). The two balanced signal terminals are disposed on both sides of the central axis of the substrate substantially perpendicular to the propagation direction of a surface acoustic wave. At least one of the first and second signal lines is disposed on the insulating film ~~formed on the substrate~~.

[0044] ——— In the above-described structure, when at least one of the first and second signal lines intersects the signal line and the connection line connecting between the IDT and the terminals excluding the balanced terminals, in this intersecting portion, a three-dimensional intersection is provided ~~performed~~ through an insulating film.

[0045] ——— According to the above-described structure, a common ~~the~~ package can be ~~commonly~~ used by arranging the balanced signal terminals at the same locations as in a surface acoustic wave filter having ~~of another configuration structure different~~ in the mode for coupling the surface acoustic wave elements. Furthermore, regarding the parasitic capacitance and bridge capacitance entering each of the two balanced signal terminals, the difference between them is reduced by disposing the signal lines connected to the balanced signal terminals on an insulating film and thus, the balancing is ~~can be~~ improved.

[0046] ——— In a surface acoustic wave device of the present invention, the characteristics are ~~can be~~ improved. For example, in the first preferred embodiment ~~case of the above-described first mode~~, the insertion loss in the passband is ~~can be~~ reduced. Furthermore, in the ~~case of the~~ second and third preferred embodiments ~~modes~~, the difference of parasitic capacitance entering each balanced signal terminal is ~~more reduced~~ as compared to ~~than in~~ the structure

described in Japanese Unexamined Patent Application Publication No. 2002-271168, Document 2 and the balancing between the balanced signal terminals is improved. Furthermore, it is becomes possible to use a common ~~commonly use the~~ package with a surface acoustic wave filter having a balanced-to-unbalanced conversion function with other configurations as ~~of another structure~~ shown in Fig. 10, Fig. 11, etc., and accordingly, it is becomes unnecessary to produce different packages ~~a package~~ for exclusive use.

[0047] Other features, elements, steps, characteristics and advantages of the present invention will become more apparent from the following detailed description of preferred embodiments of the present invention with reference to the attached drawings.

BRIEF DESCRIPTION OF THE DRAWINGS

[0048] — Fig. 1 is a top view of a balanced type SAW filter according to a first preferred embodiment of the present invention. ~~(Embodiment 1)~~

[0049] — Fig. 2 is a sectional view taken on line II - II of Fig. 1. ~~(Embodiment 1)~~

[0050] — Fig. 3 is a top view of a balanced type SAW filter according to a second preferred embodiment of the present invention. ~~(Embodiment 2)~~

[0051] — Fig. 4 is a sectional view taken on line IV - IV of Fig. 3. ~~(Embodiment 2)~~

[0052] — Fig. 5 is a top view of a balanced type SAW filter according to the related art. ~~(Related example)~~

[0053] — Fig. 6 shows the structure of a piezoelectric substrate according to the related art. ~~(Related example 2)~~

[0054] — Fig. 7 is a top view of the upper portion of a package shown in Fig. 6. ~~(Related example 2)~~

[0055] Fig. 8 is a top view of the lower portion of a package shown in Fig. 6. ~~(Related example 2)~~

[0056] Fig. 9 shows the bottom surface of a package shown in Fig. 6. ~~(Related example 2)~~

[0057] Fig. 10 shows the structure of a surface acoustic wave filter according to the related art. ~~(Reference example 1)~~

[0058] Fig. 11 shows the structure of a surface acoustic wave filter according to a reference. ~~(Reference example 2)~~

[0059] Fig. 12 shows the structure of a surface acoustic wave filter according to a reference. ~~(Reference example 3)~~

[0060] Fig. 13 is a top view of a piezoelectric substrate according to a third preferred embodiment of the present invention. ~~(Embodiment 3)~~

[0061] Fig. 14 is a diagram showing characteristics of a surface acoustic wave filter according to the third preferred embodiment of the present invention. ~~(Embodiment 3)~~

[0062] Fig. 15 is a top view of a piezoelectric substrate according to a comparative. ~~(Comparative example)~~

[0063] Fig. 16 is a top view of a piezoelectric substrate according to a fourth preferred embodiment of the present invention. ~~(Embodiment 4)~~

[0064] Fig. 17 is a top view of a piezoelectric substrate according to a fifth preferred embodiment of the present invention. ~~(Embodiment 5)~~

[0065] Fig. 18 is a top view of a piezoelectric substrate according to a reference. ~~(Reference example 1)~~

[0066] Fig. 19 is a top view of a piezoelectric substrate according to another reference. ~~(Reference example 2)~~

[0067] Fig. 20 is a bottom view of a package according to the third preferred embodiment of the present invention. ~~(Embodiment 3)~~

[0068] Fig. 21 is a top view of a piezoelectric substrate

according to a sixth preferred embodiment of the present invention.

~~{Embodiment 6}~~

[0069] — Fig. 22 is a top view of a piezoelectric substrate

according to the related art. ~~{Related example 2}~~

[0070] — Fig. 23 is a top view of a piezoelectric substrate

according to a seventh preferred embodiment of the present invention.

~~{Embodiment 7}~~

DETAILED DESCRIPTION OF PREFERRED EMBODIMENTS

[0071] Hereinafter, the preferred embodiments of the present invention are described with reference to Figs. 1 to 23.

[0072] First and second preferred embodiments are described with reference to Figs. 1 to 4.

FIRST PREFERRED EMBODIMENT

[0073] A surface acoustic wave device according to the first preferred embodiment is described with reference to Figs. 1 and 2.

Fig. 1 is a top view of a substrate 1010 in the surface acoustic wave device of the first preferred embodiment, and Fig. 2 is a sectional view taken along line II - II of Fig. 1.

Reference Numerals

~~—— 100 piezoelectric substrate~~

~~—— 101 surface acoustic wave filter element (second surface acoustic wave element)~~

~~—— 102 surface acoustic wave filter element (first surface acoustic wave element)~~

~~—— 103, 104, and 105 IDTs~~

~~—— 108, 109, and 110 IDTs~~

~~—— 118 and 119 balanced signal terminals~~

~~—— 123 and 124 signal lines~~

~~150 surface acoustic wave resonator element (second surface acoustic wave element)~~

~~250, 251, and 252 insulating films~~

~~500 piezoelectric substrate~~

~~502 surface acoustic wave filter element (surface acoustic wave element)~~

~~508, 509, and 510 IDTs~~

~~518 and 519 balanced signal terminals~~

~~523 and 524 signal lines~~

~~650 and 652 insulating films~~

~~1010 substrate~~

~~1014 and 1016 insulating films~~

~~1020 filter (first element)~~

~~1022, 1023, and 1024 IDTs~~

~~1030 filter (second element)~~

~~1032, 1033, and 1034 IDTs~~

~~1041 and 1042 wirings (signal wirings)~~

~~1048 wiring (ground wiring)~~

~~1048a, 1048b, and 1048c first layers~~

~~1048s second layer~~

~~1051 pad (unbalanced terminal)~~

~~1052 and 1053 pads (balanced terminals)~~

~~1054 and 1055 ground pads~~

~~1100 substrate~~

~~1106 and 10107 insulating films~~

~~1110 filter (first element)~~

~~1114, 116, and 118 IDTs~~

~~1120 filter (first element)~~

~~1124, 126, and 128 IDTs~~

~~1130 trap (second element)~~

~~1134 IDT~~

~~1140 trap (second element)~~

~~1144 IDT~~

~~1153 wiring (ground wiring)~~

~~1153a first layer~~

~~1153s second layer~~

~~1154 wiring (ground wiring)~~

~~1154a first layer~~

~~1154s second layer~~

~~1155, 1156, 1157, and 1158 wirings (signal wirings)~~

~~1172 ground pad (ground terminal)~~

~~1173 pad (unbalanced terminal)~~

~~1174 and 1175 pads (balanced terminals)~~

~~Best Mode for Carrying Out the Invention~~

~~Hereinafter, the embodiments of the present invention are described with reference to Figs. 1 to 23.~~

~~First, embodiments 1 and 2 are described with reference to Figs. 1 to 4.~~

~~EMBODIMENT 1~~

~~A surface acoustic wave device of an embodiment 1 is described with reference to Figs. 1 and 2. Fig. 1 is a top view of a substrate 1010 contained in the surface acoustic wave device of the embodiment 1 and Fig. 2 is a sectional view taken along line II-II of Fig. 1.~~

[0074] ~~The surface acoustic wave device according to the first embodiment 1 is preferably an EGSM receiving band filter. For example, the input impedance is about 50 Ω , the output impedance is about 150 Ω , the pass frequency band is about 925 to about 960 MHz, and the center frequency is about 942.5 MHz.~~

[0075] ~~The substrate 1010 is preferably made of a LiTaO₃ single crystal piezoelectric substrate and a metal film having a fixed pattern is provided on its main surface 1012 of the substrate 1010 as shown in Fig. 2. That is, a balanced-type SAW~~

filter is provided in which a longitudinally coupled~~longitudinal~~
~~coupling~~ resonator-type surface acoustic wave filter 1020 (hereinafter,
referred to as a filter 1020) of a first stage and a longitudinally
coupled~~longitudinal~~~~coupling~~ resonator-type surface acoustic wave
filter 1030 (hereinafter, referred to as a filter 1030) of a second
stage are cascade-connected, a pad 1051 is an unbalanced terminal, and
pads 1052 and 1053 are balanced terminals. Signal is constituted.
~~Wirings, that is, signal~~ wirings 1041 and 1042, by which the filter
1020 ~~as a first element~~ and the filter 1030~~1030 as a second element~~
are cascade-connected, intersect a ground wiring 1048 connected to an
IDT 1023 including ~~thean~~ unbalanced terminal 1051 in three dimensions.
The ground wiring 1048~~1048 to the unbalanced terminal 1051~~ is
connected to ground pads 1054 and 1055 which are disposed away from
the space contained in a place outside between the stages. The ground
pads 1054 and 1055 are ground terminals for grounding. The filters
1020 and 1030 are disposed in parallel such ~~so~~ that the propagation
direction of the surface acoustic waves is ~~may be~~ parallel to each
other.

[0076] ——— In ~~detail, in~~ the filter 1020 of the first stage, three
IDTs 1022, 1023, and 1024 are disposed in line with the propagation
direction of a surface acoustic wave and two reflectors 1021 and 1025
are disposed on either side of the IDTs 1022, 1023, and 1024. One
electrode side of the middle IDT 1023 is connected to the pad 1051 as
an unbalanced terminal through a wiring 1047. The other electrode
side is connected to the ground pads 1054 and 1055 via~~from~~ the wirings
1040 and 1048 through wirings 1043 and 1046. The sides of one
electrode of the other IDTs 1022 and 1024 are also connected to the
ground pads 1054 and 1055 through wirings 1044 and 1045.

[0077] ——— In the filter 1030 of the second stage, three IDTs 1032,
1033, and 1034 are disposed in line in the propagation direction of a
surface acoustic wave and two reflectors 1031 and 1035 are disposed on

either side of the IDTs 1032, 1033, and 1034.

[0078] —One electrode side of the middle IDT 1033 is connected to the pads 1052 and 1053 defining as balanced terminals and the other electrode is ~~made~~ a floating electrode. The sides of one electrode of the IDTs 1032 and 1034 disposed on either side of the IDT 1033 are connected to the sides of the other electrode of the IDTs 1022 and 1024 of the filter of the first stage. The sides of the other electrode of the IDTs 1032 and 1034 are connected to the ground pads 1054 and 1055 through wirings 1043 and 1046.

[0079] —Rectangular insulating films 1014 and 1016 are arranged ~~formed~~ so as to cover portions~~parts~~ of the wirings 1041 and 1042 of a signal line connecting the filters 1020 and 1030, the wiring 1048 is disposed ~~formed~~ on the insulating films 1014 and 1016, and the wirings 1041 and 1042 and the wiring 1048 intersect one another ~~through the insulating films 1014 and 1016~~ in three dimensions with the insulating films 1014 and 1016 disposed therebetween.

[0080] —In the measurements of the insulating films 1014 and 1016, the dimension in the transverse direction (in the extending direction of the wiring 1048) in the drawing is about 50 μm, the dimension in the longitudinal direction (in the extending direction of the wirings 1041 and 1042) in the drawing is about 40 to about 50 μm, and the thickness is about 2 μm. The width of the lower wirings 1041 and 1042 is about 30 μm and the width of the upper wiring 1048 is about 20 μm to about 30 μm where the wirings intersect in three dimensions. The space between the filters 1020 and 1030 is about 60 to about 70 μm. The dimensions of the ground pads 1054 and 1055 are about 100 μm × 100 μm × about 100 μm. In the related example in which the ground pads having the same dimensions are disposed~~contained~~ between the two cascade-connected longitudinally coupled~~longitudinal coupling~~ resonator-type surface acoustic wave filters, since the distance between the filters is about 200 μm, in the first preferred

embodiment-1, the distance between the filter elements is reduced
~~shortened~~ so as to be about one third or less than that in the related
example. A photosensitive resin (e.g., polyimide having a relative
dielectric constant of about 2) is preferably used for the insulating
films 1014 and 1016, for example.

[0081] —In the first preferred embodiment-1, when the wiring
1048 (also referred to as a ground wiring 1048) for the connection
of the ground pads 1054 and 1055 and the wirings 1041 and 1042 (also
referred to as signal wirings 1041 and 1042) for the connection
between the filters 1020 and 1030 intersect, the intersecting area
seen from the top is sufficiently small, the relative dielectric
constant of the insulating films 1014 and 1016 is sufficiently small
as compared to the ~~in comparison with the~~ relative dielectric constant
of the LiTaO_3 substrate 1010 which is about 50, and the thickness of
the insulating films 1014 and 1016 is sufficiently large. Accordingly,
the stray capacitance is reduced as compared to ~~can be reduced in~~
~~comparison with~~ the structure in which two elements are cascade-
connected and ground pads are disposed between the stages, as in the
related example.

[0082] —Next, the manufacturing method for the substrate 1010 is
described.

[0083] —First, an aluminum film pattern of the first layer is
formed on the main surface 1012 of the substrate 1010 by dry etching
or lift-off, for example. The aluminum film pattern of the first
layer substantially matches the final metal pattern of the IDTs, pads
and wirings, ~~etc.~~ However, as shown in Fig. 2, regarding the wiring
1048, the pattern of the first layer is not formed in the portion
where the insulating films 1014 and 1016 are formed and in the
vicinity thereof such ~~so~~ that the insulating layers 1014 and 1016 may
be disposed between the first layers 1048a, 1048b, and 1048c. The
thickness of the aluminum film of the first layer is approximately made

the same as the film thickness of the IDTs 1022 to 1024 and 1032 to 1034 and, for example, the thickness in an a-800 MHz band SAW filter is about 300 nm to about 400 nm and the thickness in a 2 GHz band SAW filter is about 150 nm to about 200 nm.

[0084] —Next, a photosensitive resin is coated and the insulating films 1014 and 1016 are formed in the intersecting portion of the wirings 1041 and 1042 between the filters 1020 and 1030 and the ground wiring 1048 ~~by using photolithography,~~ for example.

[0085] —Next, a resist mask having an opening corresponding to the final metal film pattern excluding the exposed portion of the filters 1020 and 1030 and the wirings 1041 and 1042 is formed and the aluminum film pattern of the second layer is formed ~~by using lift-off,~~ for example. Ti or NiCr as an adhesive layer may be formed between the aluminum of the first layer and the substrate 1010 or between the aluminum of the second layer and the aluminum of the first layer.

[0086] —In this mannerway, as shown in Fig. 2, the second layer 1048s of the wiring 1048 is disposed ~~put~~ on top of the first layers 1048a, 1048b, and 1048c and connected thereto. In the connection portion between the second layer 1048s and the first layers 1048a, 1048b, and 1048c, the connection portion must ~~is required to~~ have a fixed area or an area greater ~~larger~~ than that required to sufficiently reduce the connection resistance between the second layer 1048s and the first layers 1048a, 1048b, and 1048c. Accordingly, in the wiring 1048, the overlapping area between the first layers 1048a, 1048b, and 1048c and the second layer 1048s is at least about ~~made an area of~~ 20 μm ~~or more~~ per side.

[0087] The ~~It is required to connect the~~ upper wiring (second layer) of the three-dimensional intersection must be connected to the first layer connected to the IDTs at a specific ~~certain~~ location. When the signal line for connecting the two elements is disposed on the upper side of the three-dimensional intersection, a connection portion

for connecting the first layer and the second layer is ~~required~~needed between one ~~of the two element~~element and the three-dimensional intersection and between the other ~~of the two element~~element and the three-dimensional intersection. That is, ~~it is necessary to increase~~ the distance between the two elements must be increased in order to include not only the insulating film of the three-dimensional intersection, but also the connection portion between the first layer and the second layer.

[0088] ———On the other hand, when the signal lines (wirings 1041 and 1042) for connecting the two elements (filters 1020 and 1030) are disposed on the lower side of the three-dimensional intersection as in the first preferred embodiment-1, since it is not necessary to provide the connection portion between the elements and the three-dimensional intersection, the distance between the two elements is dependent upon ~~can be decided by~~ only the dimensions of the insulating film of the three-dimensional intersection.

[0089] ———In particular, in the first preferred embodiment-1, the middle IDT 1033 in the second stage is divided and configured to be connected~~constructed so as to cope~~ with a balanced output (or balanced input) and no ground wiring is required in the middle IDT 1033 in the second stage. Accordingly, regarding the ground wirings between the filters 1020 and 1030, only the ground wiring 1048 for the middle IDT 1023 in the first stage is required.

[0090] ———In the first preferred embodiment-1, the signal wirings 1041 and 1042 between the filters 1020 and 1030 are provided~~contained~~ only in the first layer and the electric resistivity of the lines is increased~~increases~~. However, the distance between the filters 1020 and 1030 is reduced~~shortened~~ and the deterioration of the insertion loss in the band is, thus, can be prevented.

[0091] ———In the surface acoustic wave device of the first preferred embodiment-1, the stray capacitance between the signal line

and the ground pads is reduced by the movement of the ground pads 1054 and 1055 from between the filters 1020 and 1030 and the insertion loss in the passband is ~~can be~~ decreased by reducing ~~making~~ the between-stage distance (that is, reducing the length of ~~smaller (that is,~~ ~~shortening~~ the signal wirings 1041 and 1042 between the filters 1020 and 1030).

SECOND PREFERRED EMBODIMENT-2

[0092] —Next, a surface acoustic wave device according to a second preferred ~~def an~~ embodiment 2 of the present invention is described with reference to Figs. 3 and 4. Fig. 3 is a top view of a substrate 1100 ~~contained in~~ the surface acoustic wave device of the second preferred embodiment, 2 and Fig. 4 is a sectional view taken on line IV - IV of Fig. 3.

[0093] —The surface acoustic wave device of the second preferred embodiment 2 is a device in which the substrate 1100 having a metal film of a fixed pattern disposed ~~formed~~ on the main surface 1102 is housed in a package (not illustrated), and may ~~can~~ be manufactured by the same method as in the first preferred embodiment 1. Hereinafter, the differences between ~~different points from~~ the first preferred embodiment and the second preferred embodiment 1 are primarily ~~mainly~~ described.

[0094] —The surface acoustic wave device of the second preferred embodiment 2 is preferably a DCS receiving band surface acoustic wave filter. For example, the input impedance is about 50 Ω , the output impedance is about 150 Ω , and the pass frequency band is about 1805 MHz to about 1880 MHz.

[0095] —As shown in Fig. 3, two sets of longitudinally coupled ~~longitudinal coupling~~ resonator-type SAW filters 1110 and 1120 (hereinafter, also referred to as filters 1110 and 1120) defining ~~as~~ first elements are connected in parallel to a pad 1173 defining ~~as~~ an

unbalanced terminal, and pads 1174 and 1175 define~~are used as~~ balanced terminals. One-port SAW resonators 1130 and 1140 (hereinafter, referred to as traps 1130 and 1140) defining~~as~~ second elements are connected in series to the filters 1110 and 1120.

[0096] —The two-element cascade connection in the longitudinally coupled longitudinal coupling resonator-type SAW filters as in the first preferred embodiment 1 has the advantage that high attenuation is achieved~~can be realized~~ outside the passband, but it is at a disadvantage in that the insertion loss in the passband is increased~~increases~~. As in the second preferred embodiment 2, high attenuation is achieved~~can be realized~~ in the vicinity of the passband by the series connection of the one-port SAW resonators 1130 and 1140 to the longitudinally coupled longitudinal coupling resonator-type SAW filters 1110 and 1120. The one-port SAW resonators 1130 and 1140 are used as trap~~staps~~ where an antiresonant frequency is located~~positioned~~ on the higher frequency side of ~~than~~ the passband of the resonator-type SAW filters 1110 and 1120.

[0097] —In ~~detail, in~~ the filters 1110 and 1120, three IDTs 1114, 1116, and 1118; and 1124, 1126, and 1128 are disposed in line in the propagation direction of a surface acoustic wave, and two reflectors 1112 and 1122 are disposed on both sides of the IDTs, respectively. One electrode side ~~sides~~ of the middle IDTs 1116 and 1126 is~~are~~ connected to a pad 1173 defining~~as~~ an unbalanced terminal through wirings 1151 and 1152, respectively. The other electrode sides are connected to a ground pad 1172 as a ground terminal through wirings 1153a and 1153, and 1154a and 1154. One electrode sides~~sides~~ of the other IDTs 1114 and 1118, and 1124 and 1128 is~~are~~ also connected to the ground pad 1172 through wirings 1150 and 1159.

[0098] —The filter 1110 is opposite in phase to the filter 1120. Furthermore, in the IDTs 1124 and 1128 of one filter 1120, the intersection is weighted so as to provide ~~for~~ adjustment of the

~~balancingbalanceig.~~

[0099] ——— In the traps 1130 and 1140, reflectors 1132 and 1142 are disposed on both sides of the IDTs 1134 and 1144. One electrode ~~sidesides~~ of the IDTs 1134 and 1144 ~~isare~~ connected to the other electrode side of the IDTs 1114 and 1118, and 1124 and 1128 of the filters 1110 and 1120 through wirings 1155 and 1156, and 1157 and 1158, respectively. The other electrode sides of the IDTs 1134 and 1144 are connected to pads 1174 and 1175 defining as balanced terminals through wirings 1160 and 1162, respectively.

[0100] ——— The wirings 1156 and 1157 ~~out of the wirings 1155 and 1156, and 1157 and 1158 by which the filters 1110 and 1120 are longitudinally connected to the traps 1130 and 1140 intersect the wirings 1153 and 1154 in three dimensions with by which the ground pad 1172 disposed in the middle is connected to the filters 1110 and 1120 through insulating films 1106 and 1107 disposed therebetween. in three dimensions.~~ Furthermore, the wirings 1151 and 1152 also intersect the wiring 1150 with the ~~through~~ insulating films 1104 and 1105 disposed therebetween.

[0101] ——— As for the dimensions of the insulating films 1104, 1105, 1106, and 1107, the dimensionmeasure in the transverse direction (extending direction of the wirings 1150, 1153, and 1154) in Fig. 3 is about 70 μm , the dimensionmeasure in the longitudinal direction (extending direction of the wirings 1151 and 1152 and perpendicular to the extending direction of the wirings 1153 and 1154) in Fig. 3 is about 40 to about 50 μm , and the thickness is about 2 μm . The width of the lower wirings 1150, 1156, and 1157 in the three dimensional intersection is about 30 μm and the width of the upper wirings 1151, 1152, 1153, and 1154 is about 20 μm to about 30 μm . The space between the filters 1110 and 1120 and the traps 1130 and 1140 is about 60 μm to about 70 μm . The dimensions of the ground pad 1172 are about 100 μm x about 100 μm ~~x 100 μm~~ . In the related example where the ground

pad of the same dimensions is disposed~~contained~~ between the filter and the trap, the space between the filter and the trap is about 200 μm , and, in the second preferred embodiment-2, the space between the filters 1110 and 1120 and the traps 1130 and 1140 is~~can be made~~ about one third or less than that in the related example.

[0102] —As shown in Fig. 4, second layers 1153s and 1154s of the wirings 1153 and 1154 are disposed~~formed~~ on the insulating layers 1106 and 1107, and the second layers 1153s and 1154s are disposed~~put~~ on the first layer 1172a of the ground pad 1172 and wirings 1153a and 1154a of only the first layer on the both sides of the insulating films 1106 and 1107. The first layer is disposed~~put~~ on the second layer in an area of at least about $20\ \mu\text{m}$ ~~or more~~ per side and both are connected.

[0103] —Moreover, the second layer is formed in the pads 1172, 1173, 1174, and 1175, the middle portion of the wiring 1150, and the wirings 1151, 1152, 1153, 1154, 1159, 1160, and 1162.

[0104] —In the second preferred embodiment-2, the three dimensional wiring is provided~~performed~~ between the filters 1110 and 1120 and the traps 1130 and 1140, but the same effect as in the first preferred embodiment may~~can~~ be obtained. That is, since the space between the two elements of the filters 1110 and 1120 and the traps 1130 and 1140 can be determined by only the dimensions of the insulating films 1106 and 1107 for three dimensional intersection, the space is relatively~~can be made~~ small.

[0105] —Since no ground wiring is required~~necessary~~ in the traps 1130 and 1140, only one ground wiring is required between the two elements for grounding the filters 1110 and 1120. Even if the wirings 1155 and 1156, and 1157 and 1158 between the two elements are provided~~performed~~ by only the first layer and the electric resistivity of the lines increases, since the distance between the two elements is reduced~~shortened~~, the deterioration of the insertion loss in the band

is can be prevented.

[0106] —Next, ~~third embodiments 3~~ to seventh preferred
embodiments 7 are described with reference to Figs. 12 to 21 and Fig.
23. Moreover, in the drawings, the same reference numerals are given
to the portions of the same structure elements as described above.

THIRD PREFERRED EMBODIMENT—3

[0107] —A surface acoustic wave filter according to a third
preferred embodiment of an embodiment 3 is described with reference to
Figs. 12 to 19 and Fig. 22. The surface acoustic wave filter of the
third preferred embodiment includes 3 ~~contains~~ a balanced-to-unbalanced
conversion function. Here, an EGSM (extended global system for mobile
communications) receiving filter in which the impedance of an
unbalanced signal terminal is about 50 Ω and the impedance of a
balanced signal terminal is about 100 Ω is described as an example.

[0108] —First, the structure of the third preferred
embodiment embodiment 3 is described with reference to Figs. 12 and 13.

[0109] —In the surface acoustic wave filter of the third
preferred embodiment 3, two longitudinally coupled longitudinal
~~coupling~~ resonator-type surface acoustic wave filter elements
(hereinafter, referred to as filter elements) 101 and 102 are provided
~~formed~~ on a piezoelectric substrate 100 and cascade connected. A
LiTaO₃, 40 \pm 5° Y-cut X-propagation substrate is preferably used as in
the piezoelectric substrate 100 and the filter elements 101 and 102
are defined ~~formed~~ by ~~using~~ aluminum electrodes.

[0110] —As ~~the basic structure is schematically shown in Fig. 12,~~
one filter element 101 includes ~~contains~~ three IDTs 103, 104, and 105
and two reflectors 106 and 107 disposed along the propagation
direction of a surface acoustic wave. The ~~other~~ IDTs 103 and 105 are
disposed ~~formed~~ so as to sandwich the middle IDT 104 and the
reflectors 106 and 107 are disposed ~~formed~~ on both sides of the IDTs

103 and 105.~~them.~~ One end of the middle IDT 104 is connected to an unbalanced signal terminal 117 by a signal line 122.

[0111] —In the same mannerway, the other filter element 102 also include~~contains~~ three IDTs 108, 109, and 110 and two reflectors 111 and 112 disposed along the propagation direction of a surface acoustic wave. The ~~other~~ IDTs 108 and 110 are disposed~~formed~~ so as to sandwich the middle IDT 109 and the reflectors 111 and 112 are disposed ~~formed~~ on both sides of the IDTs 108 and 110.~~them.~~ Both ends of the middle IDT 109 are connected to balanced signal terminals 118 and 119 by signal lines 123 and 124, respectively.

[0112] —The two filter elements 101 and 102 are cascade connected. That is, one end of the IDTs 103 and 105 ~~each~~ of the filter element 101 is connected to one end of the IDTs 108 and 110 ~~each~~ of the other element 102 via ~~by~~ signal lines 120 and 121, respectively. The other end of the IDTs 103 and 105 ~~each~~ of the filter element 101 and the other end of the IDTs 108 and 110 ~~each~~ of the other filter element 102 are grounded, respectively. Moreover, even if the other ends are connected to each other in the same mannerway as the ~~in~~ one ends, instead of being connected ~~connection~~ to the ground, there is no problem in the operation of the surface acoustic wave filter.

[0113] —The direction of each of the IDTs 103, 104, 105, 108, 109, and 110 ~~each~~ is adjusted such ~~so~~ that the phase of an electric signal transmitted on a signal line 120 connected between the IDTs 103 and 108 is approximately ~~may be about~~ 180 degrees different from the phase of an electric signal transmitted on a signal line 121 connected between the IDTs 105 and 110. Thus, excellent amplitude balancing and phase balancing of the ~~as a~~ surface acoustic wave filter is ~~can be~~ obtained.

[0114] —In the portions shown by reference numerals 113 to 116 (hereinafter, referred to as narrow-pitched electrode finger portions)

in Fig. 12, that is, in the portions between the IDTs 103 and 104 and between the IDTs 104 and 105 of ~~the~~one filter element 101 and between the IDTs 108 and 109 and between the IDTs 109 and 110 of the ~~other~~ filter element 102, the pitch of a few adjacent~~neighboring~~ electrode fingers (width of an electrode finger and space between electrode fingers) is less~~made smaller~~ than that in the other portion of the IDTs 103, 104, 105, 108, 109, and 110. Moreover, in Fig. 12, for simplicity, the number of electrode fingers is illustrated so as to be less than the actual number of electrode fingers~~ones~~. A broad bandpass filter is~~can be~~ obtained by reducing~~in such a way that~~ the discontinuity at the portions where IDTs that are adjacent to~~neighbor~~ each other is reduced~~to the maximum extent~~at most by including~~containing~~ such narrow-pitched electrode finger portions 113 to 116, and by adjusting~~that~~ the space between the IDTs 103, 104, 105, 108, 109, and 110 ~~is adjusted~~.

[0115] ———Fig. 13 shows the actual layout on a piezoelectric substrate 100. In Fig. 13, the oblique line portion having a narrow space is an electrode pattern (hereinafter, referred to as a first layer pattern) formed using~~in~~ a first photolithographic process, for example. The oblique line portion having a wide space is an electrode pattern (hereinafter, referred to as a second layer pattern) formed using~~in~~ a second photolithographic process, for example. The portions having no oblique line 250, 251, and 252 are ~~an~~ insulating films formed by~~using~~ a resin having a low dielectric constant, ~~etc.~~ before the second layer pattern is~~has been~~ formed. In Fig. 13, for brevity, the first layer pattern and the second layer pattern are illustrated so as to be in contact with each other, but actually, at least one of the first layer pattern and the second layer pattern is formed so as to be larger than the illustration in the vicinity of the location where both are in contact with each other and the second layer pattern is disposed~~put~~ on the first layer pattern to connect

both.

[0116] —The unbalanced terminal 117 is disposed in the upper middle portion of the piezoelectric substrate 100 in Fig. 13. The balanced signal terminals 118 and 119 are disposed in the lower left and right portions of the piezoelectric substrate 100 in Fig. 13, respectively. Ground terminals 201 and 202 are disposed in the upper left and right portions of the piezoelectric substrate 100 in Fig. 13, respectively. That is, the balanced signal terminals 118 and 119 are arranged disposed so as to be symmetrical about an around the imaginary central axis of the piezoelectric substrate 100.

[0117] —One terminal of the middle IDT 104 of one filter element 101 is connected to the unbalanced terminal 117 and the other terminal is connected to the ground terminal 202. One end of the IDTs 103 and 105 ~~each~~ on both sides of one filter element 101 is connected to the ground terminals 201 and 202, respectively, and the other end is connected to one end of the IDTs 108 and 110 ~~each~~ of the other filter element 102 through the signal lines 120 and 121, respectively. The connection line for connecting the other end of the middle IDT 104 to the ground terminal 202 intersects the signal line 201 in three dimensions through an insulating film 251 disposed ~~formed~~ on the signal line 121 for connecting between the IDTs 105 and 110 in the portion shown by reference numeral 203.

[0118] —The other end of the IDT 108 of the ~~other~~ filter element 102 is connected to the ground terminal 201 through the reflectors 111 and 106. That is, the other end of the IDT 108 and the reflector 111 are connected by a connection line 130, the reflectors 106 and 110 are connected by a connection line 131, and the reflector 106 and the ground terminal 201 are connected. The other end of the IDT 110 is connected to the ground terminal 202. One end of the middle IDT 109 is connected to one balanced signal terminal 118 by a signal line 123. The majority ~~Most~~ of the signal line 123 is disposed ~~formed~~ on an

insulating film 250. The signal line 123 intersects the connection line for connecting the reflectors 106 and 111 in three dimensions through the insulating film 250 in the portion shown by reference numeral 204 and intersects the signal line 120 for connecting between the IDTs 103 and 108 in three dimensions through the insulating film 250 in the portion shown by reference numeral 205. The other end of the IDT 109 is connected to the other balanced signal terminal 119 by a signal line 124. An insulating film 252 is disposed~~formed~~ between the signal line 124 and the substrate 100 and the symmetry between the balanced signal terminals is maintained.

[0119] —Next, the method for forming each pattern on the substrate 100 is described.

[0120] —First, an aluminum film pattern of a first layer is formed on the substrate 100 by a dry etching method or a lift-off method, for example. The aluminum film pattern of the first layer includes~~contains~~ the IDTs 103, 104, and 105; 108, 109, and 110, the reflectors 106 and 107; and 111 and 112, the signal lines 120 and 121, and the connection lines 130 and 131. The thickness of the aluminum film of the first layer is substantially the same in the IDTs 103, 104, and 105; and 108, 109, and 110.

[0121] —Next, a photosensitive resin is coated on the substrate 100 and the insulating films 250, 251, and 252 are formed ~~by~~ using a photolithography method, for example. Polyimide (relative dielectric constant: 2) is used as a photosensitive resin, for example. In this case, since the relative dielectric constant is sufficiently small as compared to ~~in comparison with~~ the relative dielectric constant of about 50 of the LiTaO_3 substrate 100, when the signal lines 123 and 124 connected to the balanced signal terminals 118 and 119 are formed on the insulating films 250 and 251, the stray capacitance is reduced as compared to ~~can be reduced in comparison with~~ the case in which ~~where~~ a signal line connected to a balanced signal terminal is formed

directly on a substrate.

[0122] —Next, a resist mask having an opening corresponding to the second layer pattern is formed on the substrate 100 and an aluminum film pattern of the second layer is formed ~~by~~ using a lift-off method, for example.

[0123] —Moreover, ~~Ti or NiCr as an~~ adhesive layer of, for example, Ti or NiCr may be formed between the aluminum film of the first layer and the substrate 100 or between the aluminum film of the second layer and the aluminum film of the first layer.

[0124] —In Fig. 20, the layout of external terminals 401 to 405 on the bottom surface of a package for the surface acoustic wave filter of the third preferred embodiment 3 is shown. In Fig. 20 ~~the drawing~~, the upper middle external terminal 401 is an unbalanced terminal and is connected to the terminal 117 shown in Figs. 12 and 13. The external terminals 402 and 403 in the lower right and lower left corner portions are balanced signal terminals and are connected to the terminals 118 and 119 shown in Figs. 12 and 13, respectively. The external terminals 404 and 405 in the middle portions are ground terminals.

[0125] —~~In the package, as shown in Figs. 18 and 19 shown,~~ surface acoustic wave filter element chips having a balanced-to-unbalanced conversion function with various ~~of other configurations~~ structures in which surface acoustic wave elements 71 and 72, and 81 to 84 are provided ~~formed~~ on piezoelectric substrates 70 and 80, which are substantially ~~of~~ the same size as the piezoelectric substrate 100 so as to ~~can~~ be housed in a common package. Fig. 18 corresponds to the structure shown in Fig. 10 and Fig. 19 corresponds to the structure shown in Fig. 11. In the surface acoustic wave filters having a balanced to unbalanced conversion function with ~~the~~ other configurations ~~structures~~, in the same manner ~~way~~ as the piezoelectric substrate 100 of the third preferred embodiment 3,

unbalanced terminals 73 and 87 are disposed in the upper middle portion of the piezoelectric substrates 70 and 80 ~~in the drawings~~, balanced signal terminals 74 and 75, and 86 and 85 are disposed in the lower left and right portions ~~in the drawings~~, and the ground terminals 76 and 77, 88 and 89 are disposed in the upper left and right portions ~~in the drawings~~.

[0126] —Accordingly, the surface acoustic wave filter of the third preferred embodiment ~~embodiment 3~~ and the surface acoustic wave filters having a balanced-to-unbalanced conversion function with ~~ef~~ the other configurations ~~structures~~ as shown in Figs. 18 and 19 can be housed in a common ~~have the package for common use~~.

[0127] —Moreover, in Figs. 18 and 19, the first layer pattern, the second layer pattern, and the insulating film pattern are illustrated in the same manner ~~way~~ as in Fig. 13. In Fig. 18, the signal lines between the IDTs 71b and 72b and between the IDTs 71c and 72c and the connection line for connecting between the IDT 71a and the second terminals 76 and 77 intersect in three dimensions through insulating films 78 and 79. In Fig. 19, the signal lines for connecting between the IDTs 84a and 82a and the terminal 87 and the connection lines for connecting between the IDTs 84b and ~~an~~ 82c and the terminals 88 and 89 intersect in three dimensions through insulating films 90 and 91, and the signal lines for connecting between the IDTs 83a and 81a and the terminals 86 and 85 and the connection lines for connecting between the IDTs 83b and 81c and the terminals 88 and 89 intersect in three dimensions through insulating films 92 and 93.

[0128] —Next, one example of the design ~~designing~~ of the surface acoustic wave filter elements 101 and 102 is provided ~~given~~. When the wavelength determined by the pitch of the electrode fingers where the pitch is not narrowed except in ~~for the~~ narrow-pitched electrode finger portions 113 to 116 is represented by λ_I , the following

relationship is~~relation can be~~ obtained.

Cross width: $48.1 \lambda_T$

Number of electrode fingers of filter element 101 (in the order of IDTs 103, 104, and 105): $28(6)/(6)24(6)/(6)28$ (number of narrow-pitched electrode fingers represented by the number in the parentheses)

Number of electrode fingers of filter element 102 (in the order of IDTs 108, 109, and 110): $28(6)/(3)24(3)/(6)28$ (number of narrow-pitched electrode fingers represented by the number in the parentheses)

Number of reflectors: 80

Metallization ratio: 0.70

Electrode film thickness: $0.080 \lambda_T$

[0129] ——— Fig. 14 shows the relationship between the frequency and common-mode attenuation characteristics of the above-described design example (third preferred embodiment-3). The common-mode attenuation characteristics show the balancing between balanced signal terminals, and that as, ~~the more~~ the attenuation increases, the ~~better the~~ balancing between balanced signal terminals improves~~becomes~~.

[0130] ——— In Fig. 14, as a comparative example, the relationship between the frequency and common-mode attenuation characteristics ~~in the case where~~ an extra wiring for balanced signal terminals is included~~are contained~~ inside a package as in Japanese Unexamined Patent Application Publication No. 2002-271168~~Document-2~~ and the layout of the terminals on the bottom surface of the package is ~~made~~ the same as that shown in Fig. 20~~are shown~~. The layout on the piezoelectric substrate of the comparative example is shown in Fig. 15. The specification of the filter elements 101 and 102 is the same as that of the above design example (third preferred embodiment). ~~-3-~~ In Fig. 15 show~~showing~~ the layout on a piezoelectric substrate 300 in which, an unbalanced signal terminal 117' is disposed in the upper

middle portion, a balanced signal terminal 118' is disposed on the slightly right side from the middle, and a balanced signal terminal 119' is disposed on the lower right portion. A ground terminal 301 is disposed in the upper left portion, a ground terminal 302 is disposed in the upper right portion, a ground terminal 303 is disposed on the slightly left side from the middle, and a ground terminal 304 is disposed in the lower left portion.

[0131] ———The passband of the EGSM receiving filter is about 925 MHz to about 960 MHz. In Fig. 14, when the ~~greatest~~largest common-mode attenuation is compared in the frequency band, although the common-mode attenuation is about 24.0 dB in the comparative example, the common mode attenuation is about 27.5 dB in the preferred embodiment and, as a result, the common mode attenuation improves by about 3.5 dB as compared to~~in comparison with~~ the comparative example.

[0132] One of the ———~~Regarding main causes of this why such an effect is that can be obtained, for one thing,~~ since the asymmetrical extra wiring connected to the balanced signal terminals in the comparative example is not provided in the preferred embodiment~~made unsymmetrical different from in the comparative example,~~ the difference of the effect~~affect~~ of parasitic capacitance,~~etc.,~~ is eliminated, and, ~~for another thing, since,~~ in the preferred embodiment, the signal lines 123 and 124 for connecting between the IDTs and the balanced signal terminals on the piezoelectric substrate are provided on an insulating film pattern made of a resin having~~of~~ a low dielectric constant, even if the lengths of the signal lines 123 and 124 are~~is~~ different from each other on the piezoelectric substrate, ~~it is considered that~~ the difference of the parasitic capacitance entering each balanced terminal is minimal~~small~~.

[0133] ———As ~~is~~ described above, according to the third preferred embodiment-3, when the terminals of the middle IDT in the three IDTs in a longitudinally coupled~~longitudinal coupling~~ resonator-type

surface acoustic wave filter having three IDTs are connected to balanced signal terminals, ~~respectively, in the surface acoustic wave filter having a balanced to unbalanced conversion function,~~ a filter having an greatly improved~~excellent~~ balancing between the balanced signal terminals is~~can be~~ obtained ~~in comparison with the related method.~~ Furthermore, the above-described surface acoustic wave filter and a surface acoustic wave filter having a balanced to unbalanced conversion function of another configuration can be housed in a common structure~~can share the package.~~

[0134] —Next, fourth~~other~~ ~~embodiments 4 to seventh preferred embodiments 7~~ are described. The fourth~~In the~~ ~~embodiments 4 to seventh preferred embodiments achieve~~7, the same effects as those achieved in the third preferred embodiment~~3 can be obtained.~~

Hereinafter, the differences between~~different points from~~ the fourth to seventh preferred embodiments and the third preferred embodiment ~~3~~ are primarily~~mainly~~ described.

FOURTH PREFERRED EMBODIMENT—4

[0135] —The signal lines 123 and 124 are disposed~~formed~~ on the insulating films 250 and 251 in the third preferred embodiment. ~~However 3, but,~~ in the fourth preferred embodiment—4, as shown in Fig. 16, only the longer signal line 123 is disposed~~contained~~ on the insulating film 250.

FIFTH PREFERRED EMBODIMENT—5

[0136] —As shown in Fig. 17, the connecting method between the IDT 108 and the ground terminal is different from that in the third preferred embodiment—3. That is, there is no connecting line for connecting between the IDT 108 and the reflector 111, between the reflectors 106 and 111, and between the reflector 106 and the ground terminal 201. Instead, for connecting to the ground terminal 202, a

connection line 132 for connecting to the IDT 108 is ~~defined~~^{formed} by the first layer pattern. The connection line 132 is connected to a connection line of the second layer pattern for connecting between the IDT 110 and the ground terminal 202. The insulating film 252 is ~~provided~~^{formed} on the connection line 132 and intersects the signal line 124 for connecting between the middle IDT 109 and a balanced signal terminal 119 in three dimensions.

SIXTH PREFERRED EMBODIMENT—6

[0137] —As shown in Fig. 21, a surface acoustic wave resonator element (hereinafter, referred to as a resonator element) 150 is connected in series to the filter element 102. Also in this case, the attenuation outside the passband ~~is~~ ^{can be} increased in the same ~~mannerway~~ as in the third to fifth preferred embodiments in which ~~embodiments 3 to 5 where~~ the two longitudinally coupled ~~longitudinal coupling~~ resonator-type surface acoustic wave filter elements are cascade connected.

[0138] —In the resonator element 150, reflectors 152 and 153 are disposed on both sides of an IDT 151. One end of the IDT 151 is connected to an unbalanced signal terminal 117 and the other end is connected to one ends of the IDTs 108 and 110 of the filter element 102 by signal lines 120' and 121'.

[0139] —The pattern of the first layer ~~includes~~^{contains} the filter element 102, the resonator element 150, the signal lines 120' and 121', the connection line 130 between the IDT and the reflector 111, and a connection line 131' extending from the reflector 111 to the middle on the side of the resonator element 150. The connection line 131' extending to the middle on the side of the resonator element 150 is connected to the ground terminal 201 by the connection line of the second layer pattern. The signal line 123 for connecting between the IDT 109 of the filter element 102 and the balanced terminal 118

intersects the signal line 120' and the connection line 131' in three dimensions through the insulating film 250.

[0140] ———In the resonator element 150, one end of the IDT 151 is connected to the ground terminal 201 or 202, the other end connected to the filter 102 is connected to the unbalanced terminal 117 by the signal lines 120' and 121', and the resonator element 105 may be connected in parallel to the filter element 102.

[0141] ———Furthermore, in the resonator 150, a plurality of resonator elements may be connected in series or in parallel.

SEVENTH PREFERRED EMBODIMENT—7

[0142] ———As shown in Fig. 23, only one filter element 502 is disposed on a piezoelectric substrate 500. Also in this case, a filter having greatly improved~~an excellent~~ balancing between balanced signal terminals 518 and 519 ~~is~~can be obtained in ~~comparison with the related method in the same manner~~way as in the third through sixth preferred embodiments—3 to 6. Furthermore, the filter and a surface acoustic wave filter having a balanced to unbalanced conversion function of another configuration can be housed in a common structure ~~can have the package for common use~~.

[0143] ———The filter element 502 includes~~contains~~ reflectors 511 and 512 on both sides of three IDTs 508, 509, and 510. One end of the ~~Out of the IDTs 508 and 510 on both sides, one end of one~~ IDT 508 is connected to a signal line 520' and one end of the ~~other~~ IDT 510 is connected to a signal line 521'. The signal lines 520' and 521' are connected to an unbalanced terminal 517 by a connection line of the second layer pattern.

[0144] ———The pattern of the first layer includes~~contains~~ the filter element 502, the signal lines 520' and 521', and a connection line 530 for connecting between the other end of the IDT 508 and the reflector 511. A connection line 531' extending to the middle from

the reflector 511 is connected to a ground terminal 601 by the connection line of the second layer pattern. The other end of the IDT 510 is connected to a ground terminal 602 by the connection line of the second layer pattern. A signal line 523 for connecting between one end of the IDT 509 of the filter element 502 and one balanced terminal 518 intersects the signal line 520' and the connection line 531' in three dimensions through an insulating film 650. An insulating film 652 is also provided~~formed~~ between a signal line 524 for connecting between the other end of the IDT 509 of the filter element 502 and the other balanced terminal 519 and the piezoelectric substrate 500.

[0145] —As described above, in the surface acoustic wave filter of the ~~third~~~~embodiments 3~~ to seventh preferred embodiments⁷, since the layout of each terminal (bump) disposed~~formed~~ on the piezoelectric substrate can be made substantially the same as each terminal (bump) in the element chip of a surface acoustic wave filter of another configuration~~structure~~, the above-described surface acoustic wave filter and the surface acoustic wave filter of another configuration can be housed in a common ~~structure can have the package for common~~ use.

[0146] —Furthermore, since the differences in the routes~~difference by route~~ between signal lines in an element chip are ~~can be~~ substantially reduced by providing~~forming~~ signal lines connected to balanced signal terminals on an insulating film pattern provided~~formed~~ on a piezoelectric substrate, balancing is greatly ~~can be~~ improved without providing the different routes~~route difference~~ in a package.

[0147] —According to the first~~embodiments 1~~ to seventh preferred embodiments⁷, characteristics of a surface acoustic wave device are ~~greatly~~~~can be~~ improved.

[0148] —Moreover, the present invention is not limited to the

above-described preferred embodiments, ~~and~~but various modifications can be ~~made~~performed.

[0149] For example, other than~~except for~~ LiTaO₃, a single crystal substrate of quartz, LiNbO₃, or other suitable materials~~etc.~~, can be used as a substrate. Furthermore, the present invention can be applied to a surface acoustic wave device using a piezoelectric thin film of ZnO, AlN, or other suitable piezoelectric thin films~~etc.~~.

[0150] For example, although a 40 ± 5°Y-cut X-propagation LiTaO₃ substrate is used in the ~~third~~embodiments 3 to seventh preferred ~~embodiments 7~~, in the present invention, the substrate is not limited thereto, and~~to, but~~ the same effect can be obtained by using a substrate of 64 to 72° Y-cut X-propagation LiNbO₃, 41°Y-cut X-propagation LiNbO₃, or other suitable substrates~~etc.~~.

[0151] Furthermore, the present invention can be applied to not only a surface acoustic wave filter of a structure having a balanced-to-unbalanced conversion function, but also to a ~~surface acoustic wave filter of a surface acoustic wave filter~~structure having a balanced-to-balanced conversion function.

[0152] While preferred embodiments of the present invention have been described above, it is to be understood that variations and modifications will be apparent to those skilled in the art without departing the scope and spirit of the present invention. The scope of the present invention, therefore, is to be determined solely by the following claims.